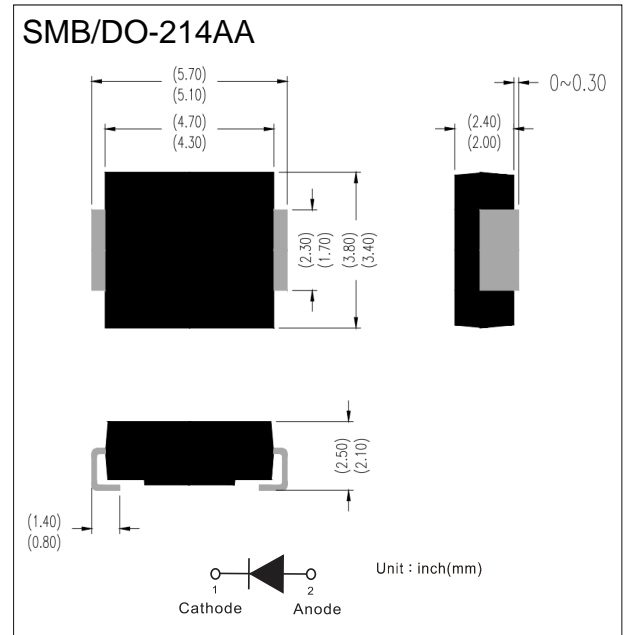


■ **Features**

- Glass passivated junction chip
- Ideal for automated placement
- Low forward voltage drop
- High surge current capability

■ **Mechanical Data**

- package:SMB/DO-214AA
- Polarity: Indicated by cathode band
- Epoxy: UL 94V-0 rate flame retardant
- Mounting Position : Any



■ **Absolute Maximum Ratings**( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

PARAMETER	SYMBOL	S3A	S3B	S3D	S3G	S3J	S3K	S3M	UNIT
Repetitive peak reverse voltage	$V_{RRM}$	50	100	200	400	600	800	1000	V
Reverse voltage, total rms value	$V_{R(RMS)}$	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	$V_{DC}$	50	100	200	400	600	800	1000	V
Forward current	$I_{F(AV)}$	3							A
Surge peak forward current, 8.3 ms single half sine-wave superimposed on rated load per diode	$I_{FSM}$	80							A
Junction temperature	$T_J$	- 55 to +150							$^{\circ}\text{C}$
Storage temperature	$T_{STG}$	- 55 to +150							$^{\circ}\text{C}$

■ **Thermal Performance**( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-lead thermal resistance	$R_{\theta JL}$	10	$^{\circ}\text{C/W}$

■ Electrical Specifications ( $T_A=25^\circ\text{C}$  unless otherwise noted)

PARAMETER	CONDITIONS	SYMBOL	TYP	MAX	UNIT
Forward voltage per diode <sup>(1)</sup>	$I_F = 3\text{A}, T_J = 25^\circ\text{C}$	$V_F$	-	1.15	V
Reverse current @ rated $V_R$ per diode <sup>(2)</sup>	$T_J = 25^\circ\text{C}$	$I_R$	-	10	$\mu\text{A}$
	$T_J = 125^\circ\text{C}$		-	250	$\mu\text{A}$
Junction capacitance	1 MHz, $V_R=4.0\text{V}$	$C_J$	40	-	pF
Reverse recovery time	$I_F=0.5\text{A}, I_R=1.0\text{A}$ $I_{RR}=0.25\text{A}$	$t_{rr}$	1500	-	ns

Notes:

1. Pulse test with  $PW=0.3\text{ ms}$
2. Pulse test with  $PW=30\text{ ms}$

■ Characteristics Curves ( $T_A=25^\circ\text{C}$  unless otherwise noted)

Fig.1 Forward Current Derating Curve

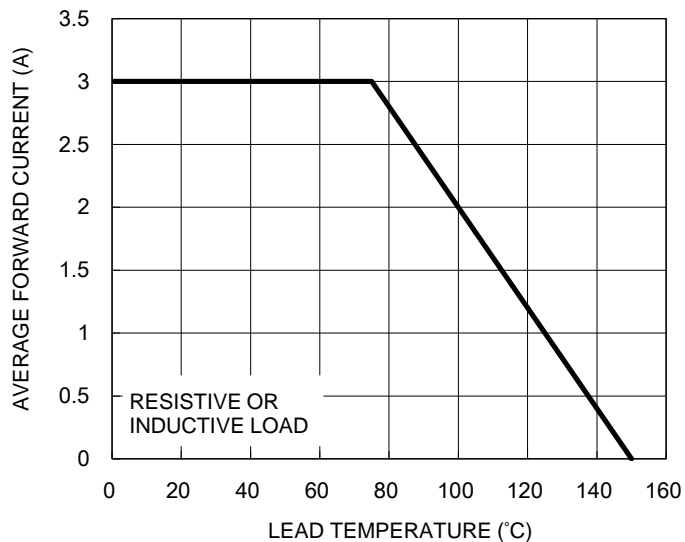


Fig.2 Typical Junction Capacitance

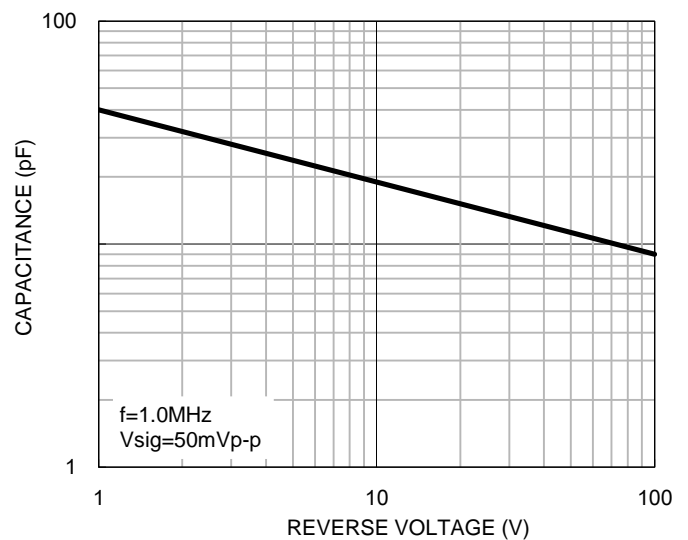




Fig.3 Typical Reverse Characteristics

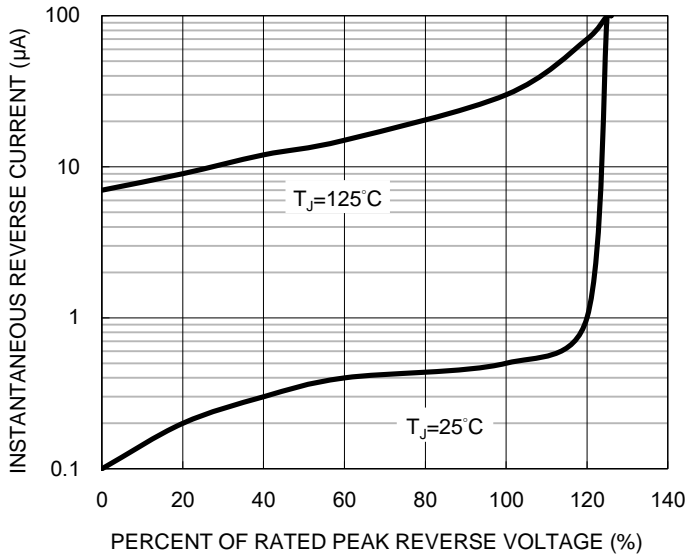


Fig.4 Typical Forward Characteristics

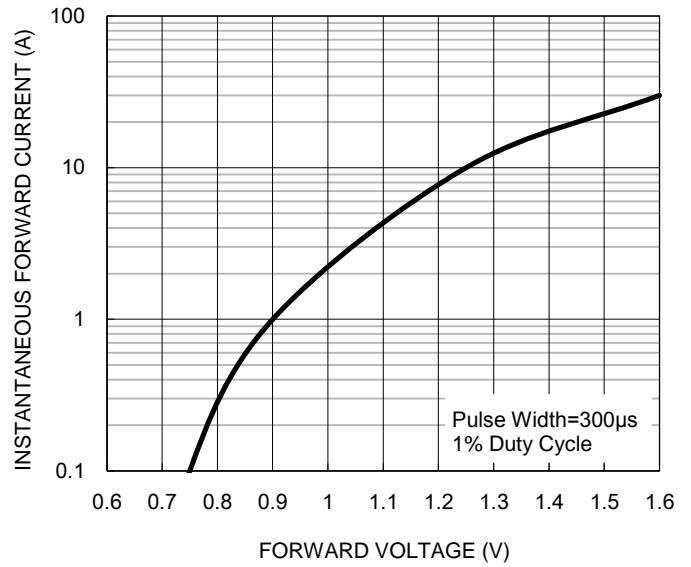


Fig.5 Maximum Non-repetitive Forward Surge Current

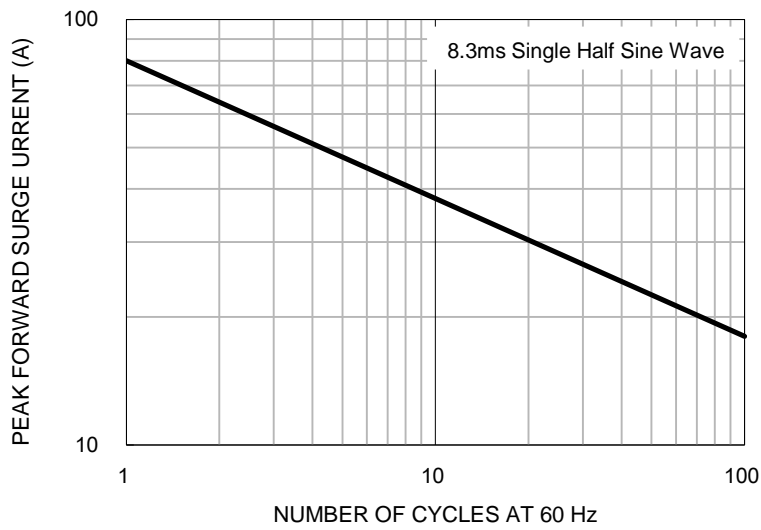
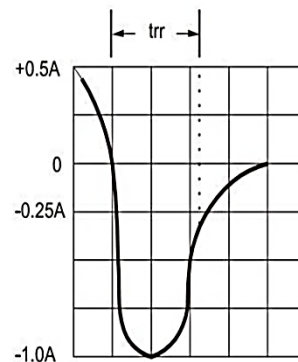
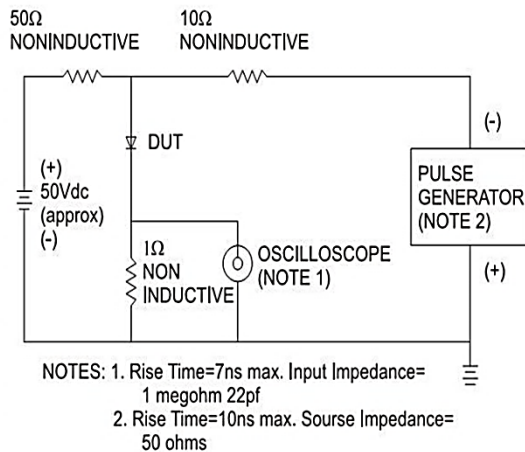


Fig.6 Reverse Recovery Time Characteristic And Test Circuit Diagram



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